

CentralTM Semiconductor Corp.

145 Adams Avenue, Hauppauge, NY 11788 USA
Tel: (631) 435-1110 • Fax: (631) 435-1824

Manufacturers of World Class Discrete Semiconductors

1N270
1N277
1N281
1N283
GERMANIUM DIODE
JEDEC DO-7 CASE

The CENTRAL SEMICONDUCTOR 1N100A, 1N270, 1N277, 1N281, 1N283 types are Gold Bonded Germanium Diodes mounted in a hermetically sealed glass case, designed for general purpose application. Special devices with a higher breakdown voltage and/or lower leakage limits are available on special order.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

	SYMBOL	1N100A	1N270	1N277	1N281	1N283	UNIT
Peak Repetitive Reverse Voltage	V_{RRM}	80	80	100	60	20	V
D.C. Forward Current	I_F			100			mA
Peak Forward Current	I_{FM}			350			mA
Peak Forward Surge Current(1.0s)*	I_{FSM}			500			mA
Power Dissipation**	P_D			80			mW
Operating and Storage Junction Temperature	T_J, T_{STG}		-65 TO +100				$^\circ\text{C}$

*Non-recurrent

**Derate above 25°C 10mW/ 10°C

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	1N100A		1N270		1N277		1N281		1N283		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
I_R	$V_R=10V$		-		-		10		30		20	μA
I_R	$V_R=50V$		50		100		50		500		-	μA
BV_R	$I_R=1.0\text{mA}$	80		80		100		60		20		V
V_F	$I_F=40\text{mA}$		1.0		-		-		-		-	V
V_F	$I_F=100\text{mA}$		-		-		1.0		1.0		-	V
V_F	$I_F=200\text{mA}$		-		1.0		-		-		1.0	V

